

ABSTRACT OF THE DISCLOSURE

In a nonvolatile memory cell having at least two floating gates, each floating gate (160) has an upward protruding portion. This portion can be formed as a spacer over a sidewall of the select gate (140). The spacer can be formed from a layer (160.2) deposited
5 after the layer (160.1) which provides a lower portion of the floating gate. Alternatively, the upward protruding portion and the lower portion can be formed from the same layers or sub-layers all of which are present in both portions. The control gate (170) can be defined without photolithography. Other embodiments are also provided.